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Power Matters™

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## Overview **Diagrams**

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>			1.00	V
DC Current Gain	HFE	20.00		80.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			120.00	V
Collector Current (dc)	I <sub>C</sub>			16.00	А
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>			120.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			7.00	V
Power Dissipation, Total	P <sub>T</sub>			200.00	W

This part can be found in the following product categories:

- Discretes ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ PNP Transistor
- $\bullet \ \ \, \text{Non-Radiation Hardened Devices} \ \bullet \ \, \text{Transistors} \ \bullet \ \, \text{BJT(BiPolar Junction Transistor)} \ \bullet \ \, \text{NPN Transistor}$

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